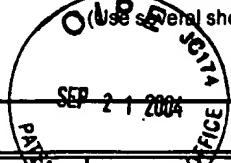


<p>FORM PTO-1449 U.S. Department of Commerce (Rev. 4/92) Patent and Trademark Office</p> <p>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</p> <p><input checked="" type="radio"/> (Use several sheets if necessary)</p> <p style="text-align: right;">SEP 2 1 2000</p>	ATTY. DOCKET NO.	SERIAL NO.
	JEL31015	912 09/511,592
	APPLICANT	Tatau NISHINAGA
FILING DATE	GROUP	
February 23, 2000	1766 1728	



U.S. PATENT DOCUMENTS

FOREIGN PATENT DOCUMENTS

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

Fifth	German Office Action dated June 21, 2004 with English translation.
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Fifth	B-Y. TSAUR, et al.; "Low-dislocation-density GaAs epilayers grown on Ge-coated Si substrates by means of lateral epitaxial overgrowth", Appln. Phys. Lett. 41(4), 15 August 1982, pp. 347-349.
Fifth	Y. MATSUNAGA, et al.; "Microchannel Epitaxy of GaAs ON Si(100) Substrates Using SiO ₂ Shadow Masks", Electrochemical Society Proceedings Volume 97-21 (1997), pp. 184-188.

EXAMINER

G. H. Fisher

DATE CONSIDERED

3/21/2006

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